

3DX: A micromachined silicon crystallographic X-ray detector

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- Tests conducted at ALS 10.3.1 (Al Thompson)
- Tests conducted at ESRF ID18F (John Morse)
- Tests conducted at ALS 4.2.2 (Ed Westbrook)

***Protein crystallography* detectors now:**

**Phosphor screen, with fiber-optic coupling to multi-CCD readout.
~200 x 200mm² square and with spatial PSF ~200μm
(FWHM)**

- Intense diffraction spots in image spoil the usable dynamic range (which in any case never exceeds "16 bits")
- *Sample is rapidly destroyed in the X-ray beam ($>10^{13}$ photons/sec).*
CCD systems require a few seconds to readout, while strongly diffracting crystals can saturate the CCD in 0.1sec
- Long tails associated with the wide spatial response of the phosphor screen+optics. This limits the precision of flat field correction and the measurement of signal intensities of closely grouped diffraction peaks

→ 3DX pixel detector benefits:

Direct absorption in silicon:

Single photon sensitivity

(Pseudo) counting detector: dynamic range??

Quasi-continuous ($64\mu\text{s}$ periodic) readout

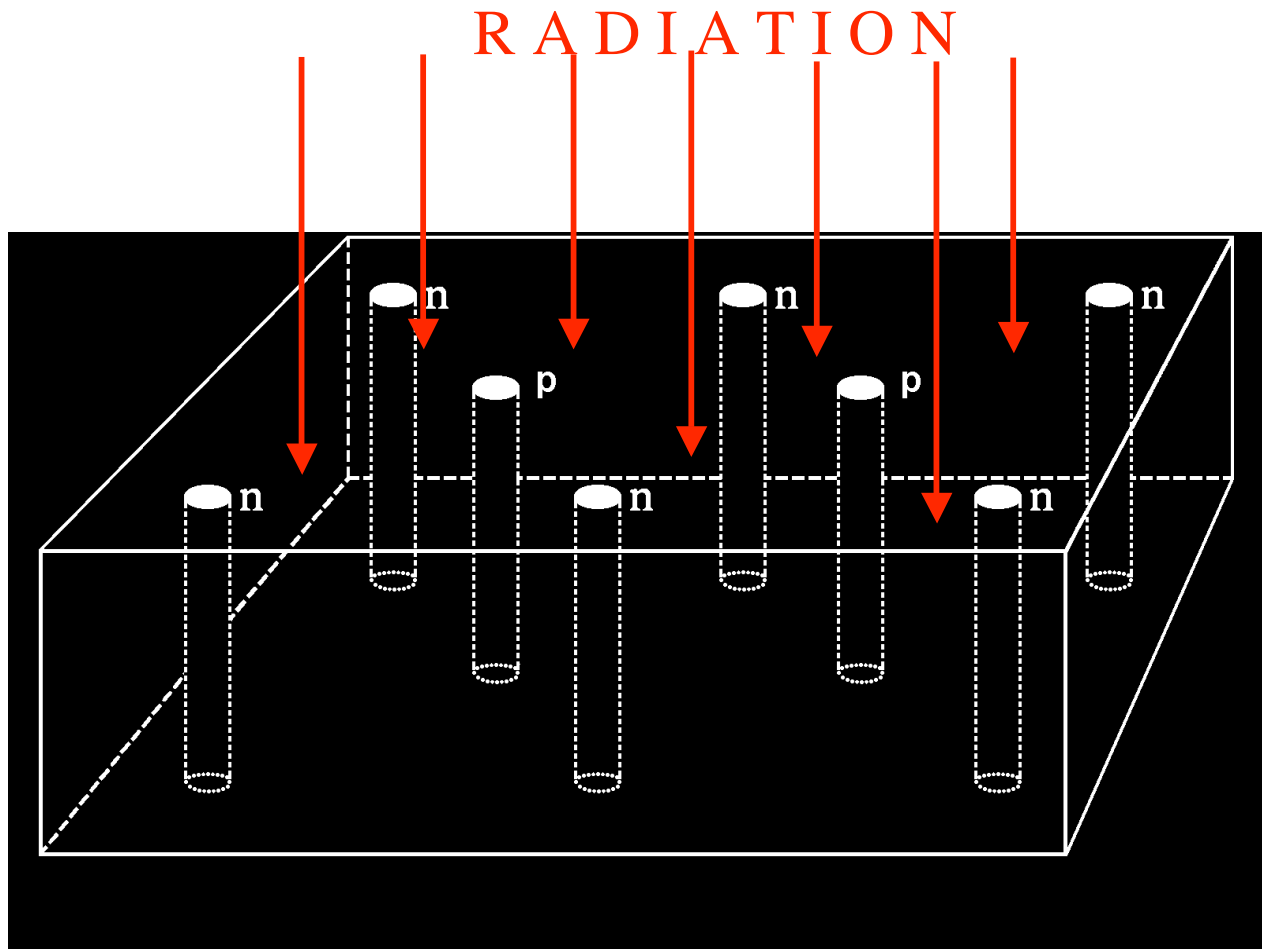
'Single pixel' point response function ($150\mu\text{m}$)

*Use 3D silicon with active edges => large area can then be covered with small sensors (yield!) with **no insensitive border areas***

3D* detectors

Column electrodes penetrate through the semiconductor substrate. Electrode spacing choice is independent of the substrate thickness.

*S. Parker, C. Kenney, J. Segal, *Nucl. Instrum. and Meth.* **A395** (1997), 328-343.

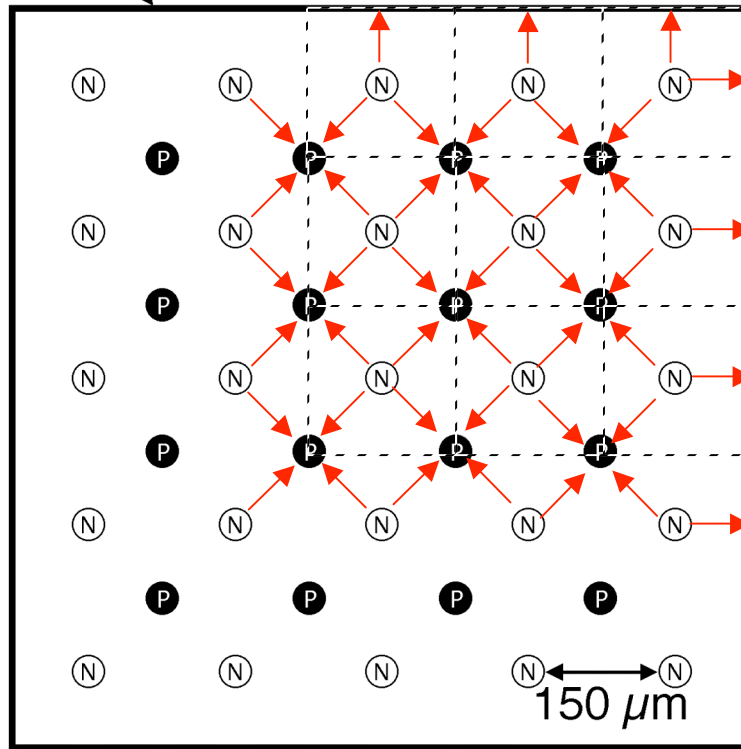


Electrode geometry for the 3DX pixel detector

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edge is p-type polycrystalline silicon ("poly")



Active edge pixels

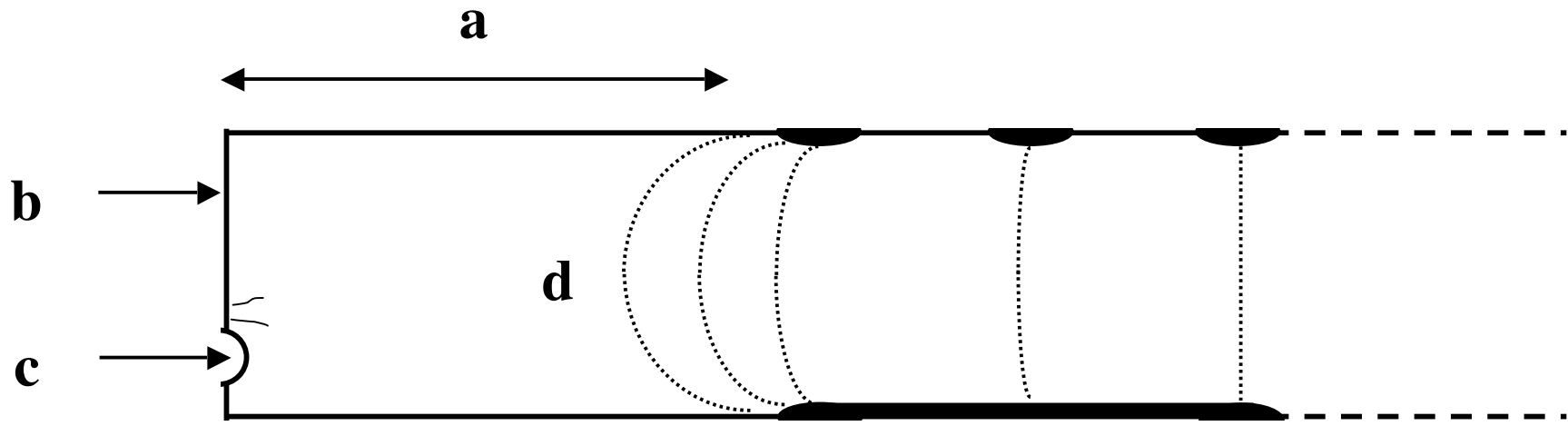
edge same potential as p-type electrodes

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3D Compared to planar PIN diodes:

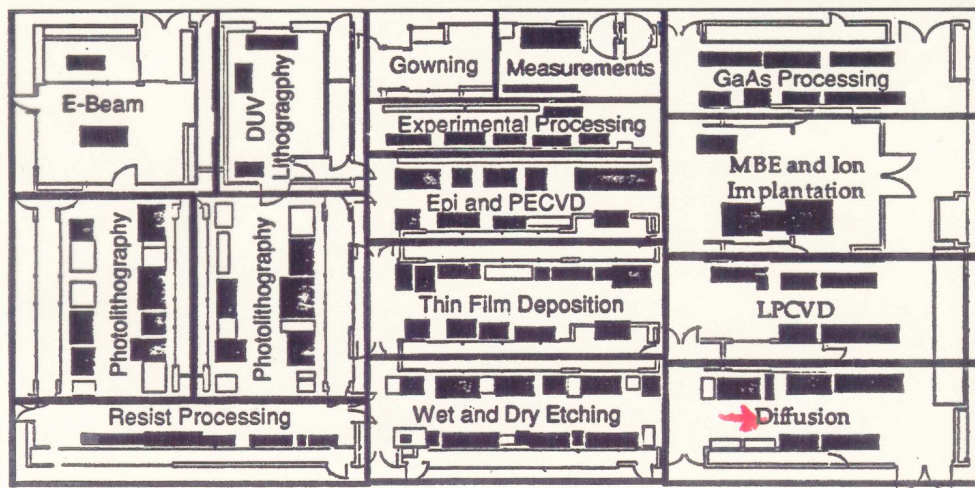
- **order-of-magnitude faster signal risetime**
- **greater resistance to bulk radiation damage**
- **minimal 'charge sharing' between pixels**
- **'active edge' electrodes eliminate dead borders around the cut edges of planar processed diodes.**



Schematic cross-section view of a standard sensor edge, showing some reasons for the insensitive region there: (a) space may be needed for guard and voltage-dropping rings, (b) the saw-cut edges are conducting, and (c) often contain chips or small cracks, all of which must remain clear of (d), the bulge of the edge of the electric field in the depleted region.

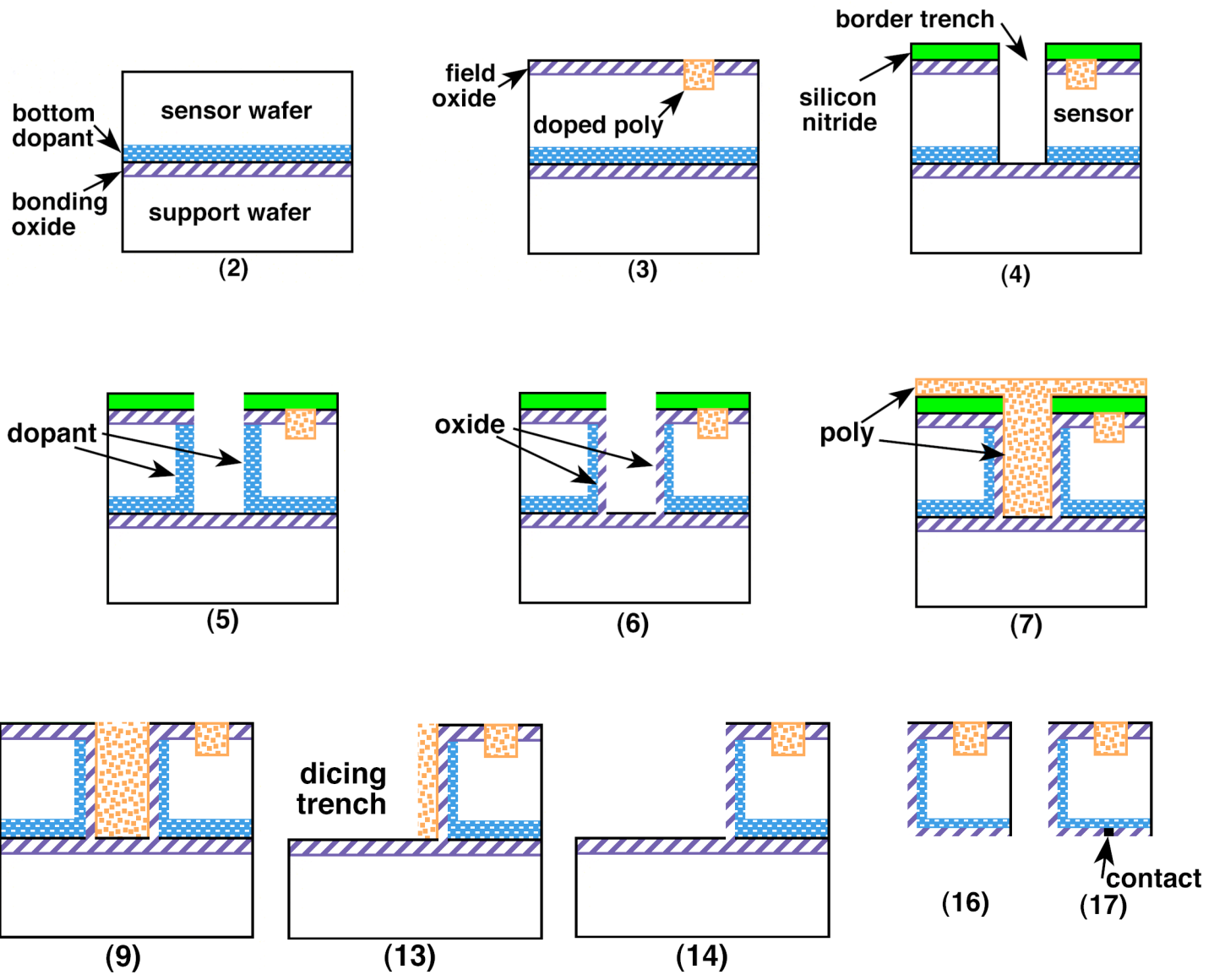


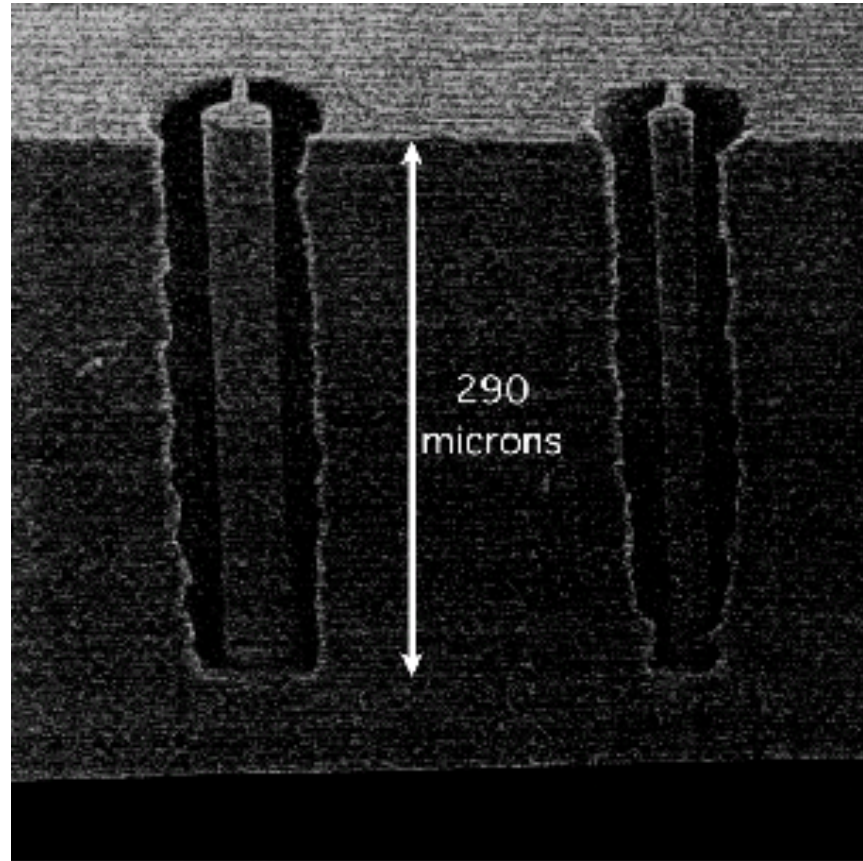
The Stanford Nanofabrication Facility



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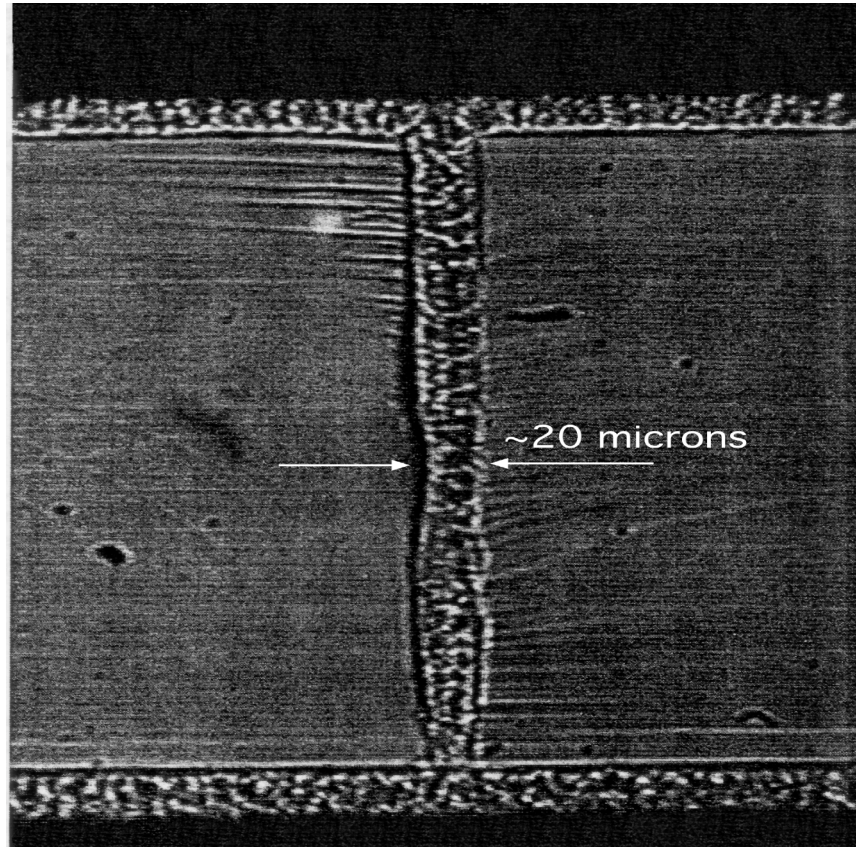




'C' hole structures in silicon, fabricated at Stanford Nano-Fabrication Facility using Bosch process (inductively coupled SF₆ plasma etching)

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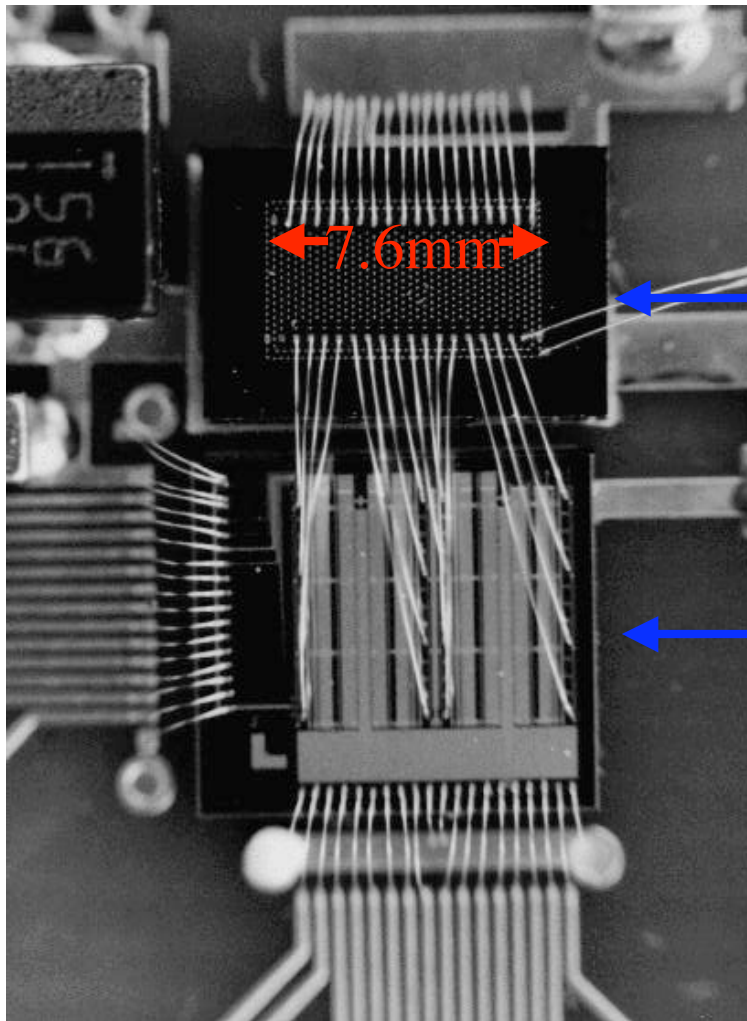




'Cracked' 3D detector, revealing doped polycrystalline silicon column electrode 20 μ m diameter

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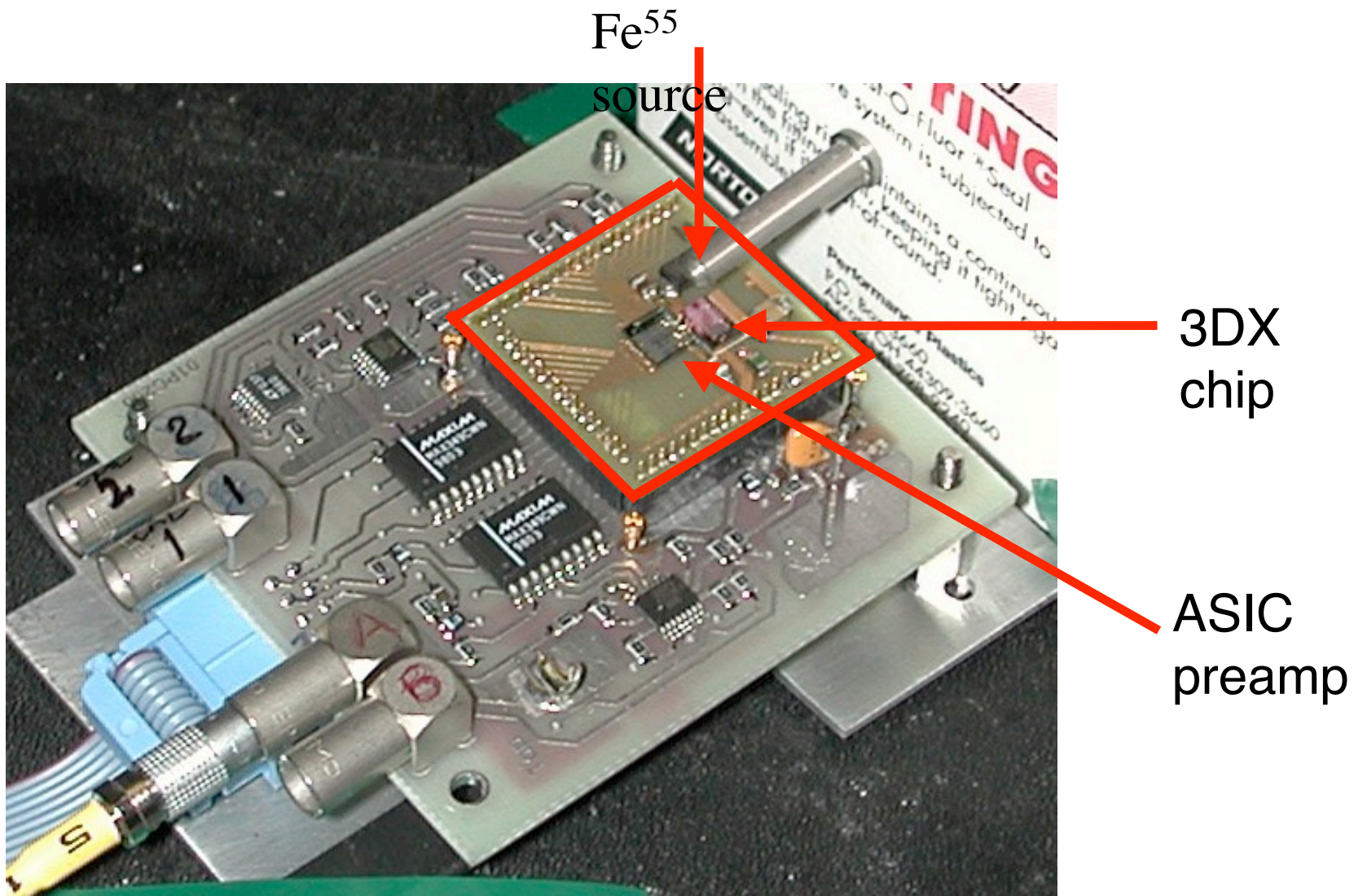


3DX chip

8 channel
charge
preamp
and shaper

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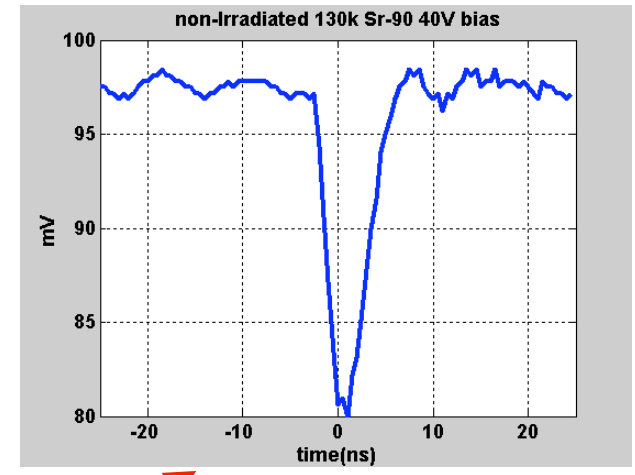
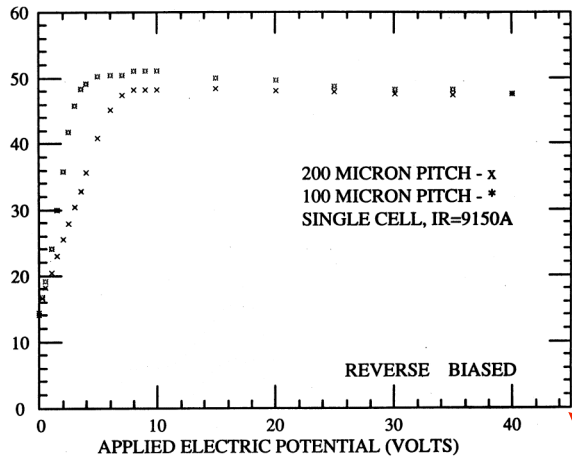




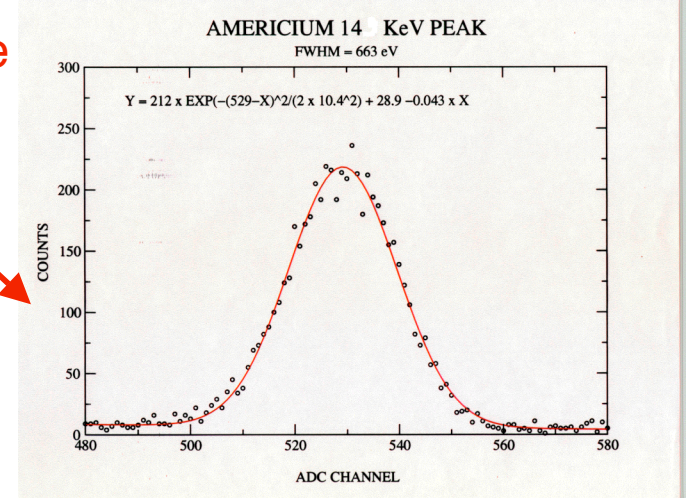
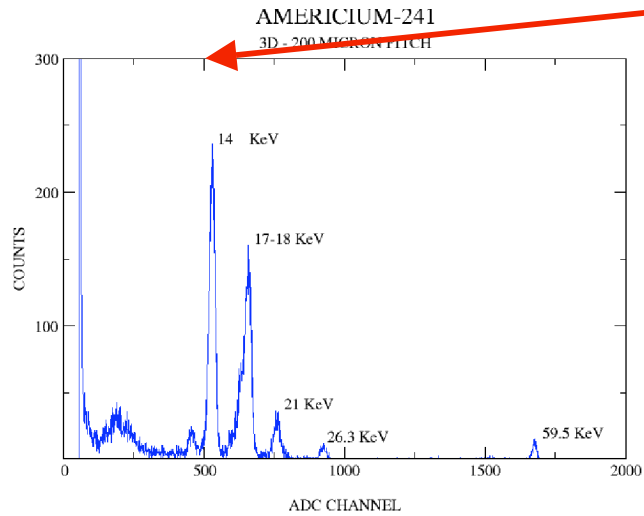
3DX chip + 8 channel charge preamplifier test board

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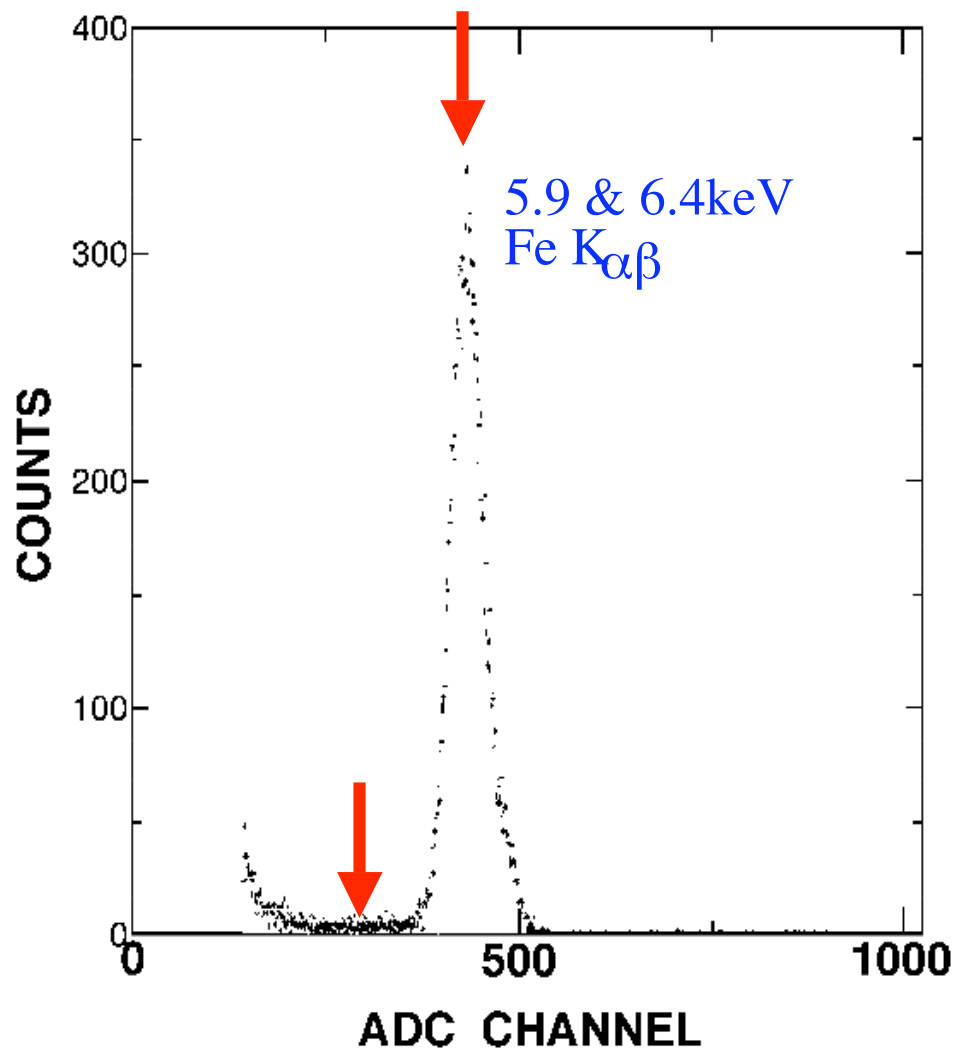


- ❖ Small V_{FD} 5-8 V
- ❖ Speed 1.5, 3.5 ns
- ❖ Energy resolution
- ❖ Gaussian response



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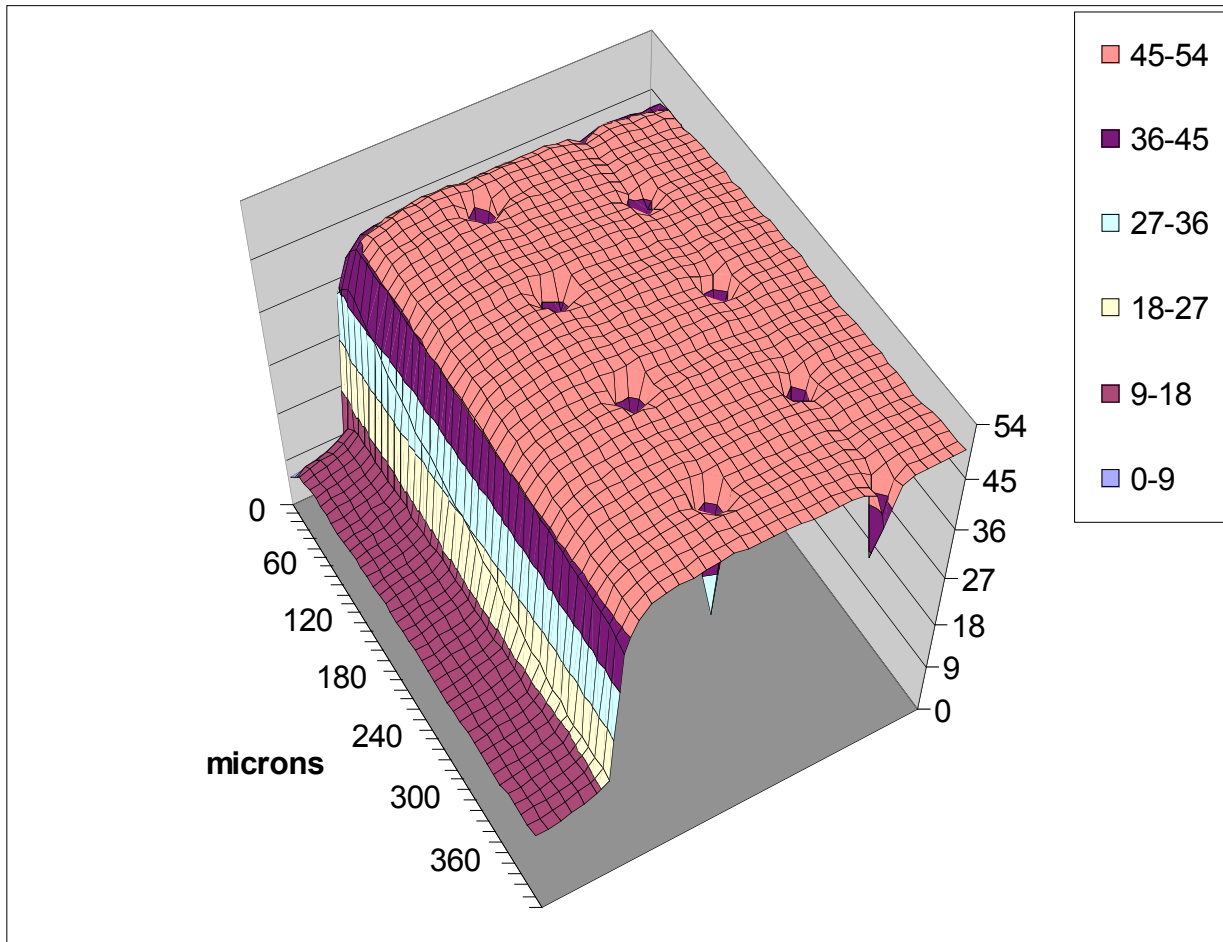




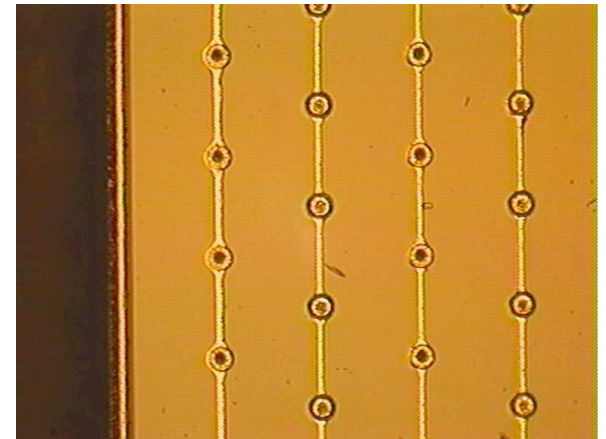
Flood exposure
to ^{55}Fe iron
source

Fe K α , K β
fluorescence lines
not separated due
to 620eV ASIC
preamplifier noise

- 12 KeV X Rays at ALS

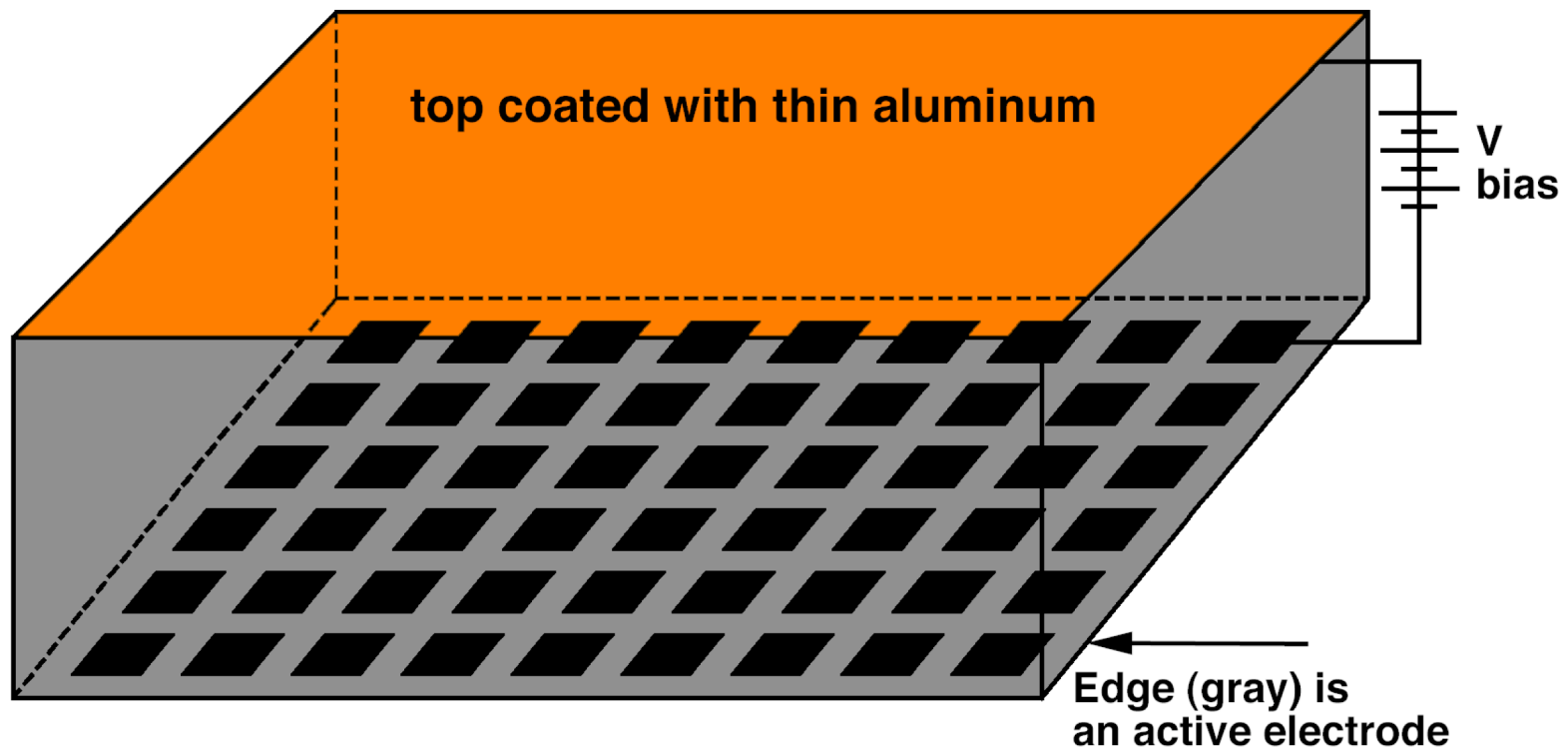


Beamline 10.3.1
~ 1 μm focused spot

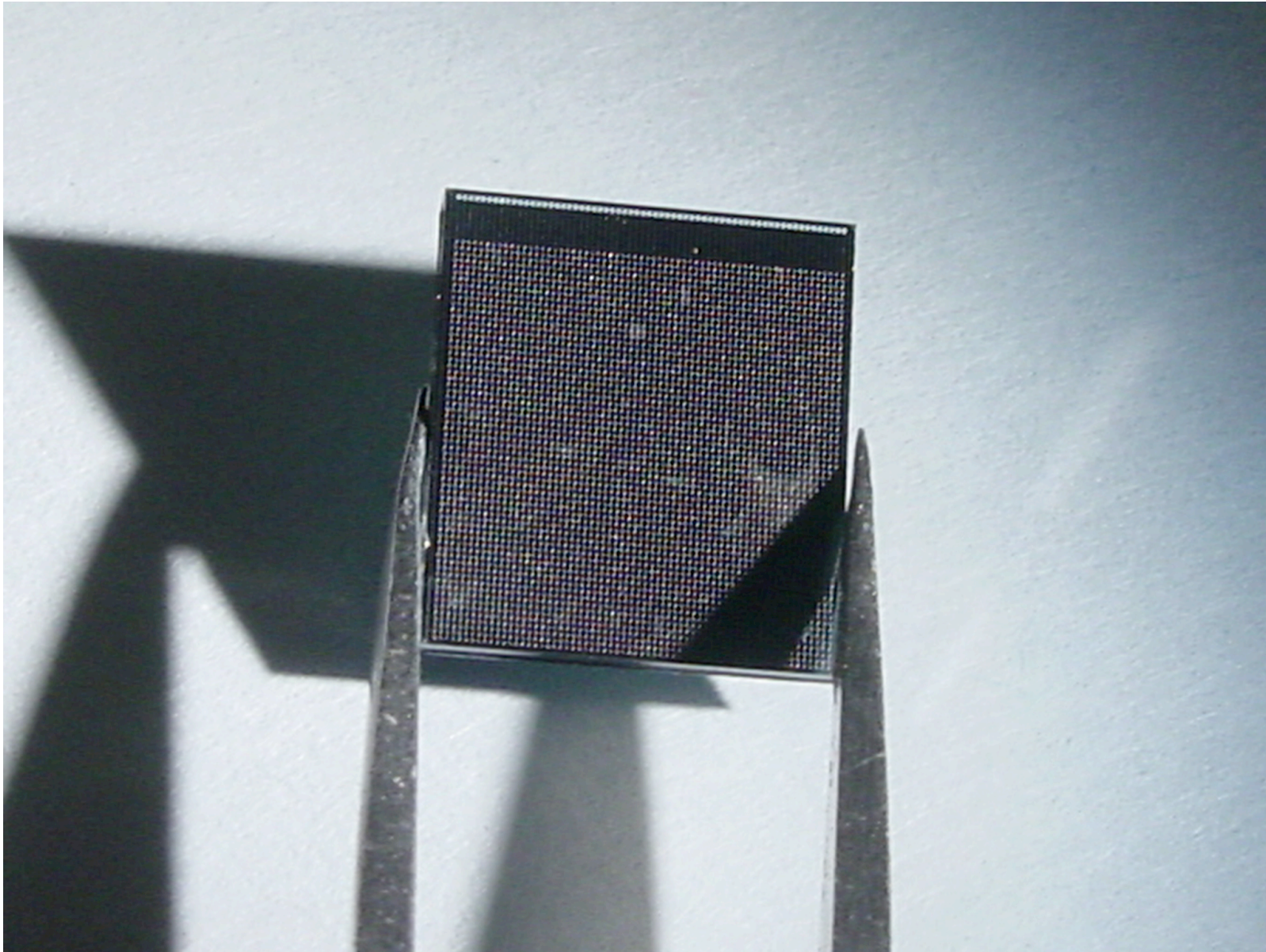


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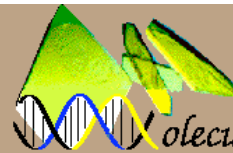


“Planar 3D” devices have active edges, but no Internal electrodes

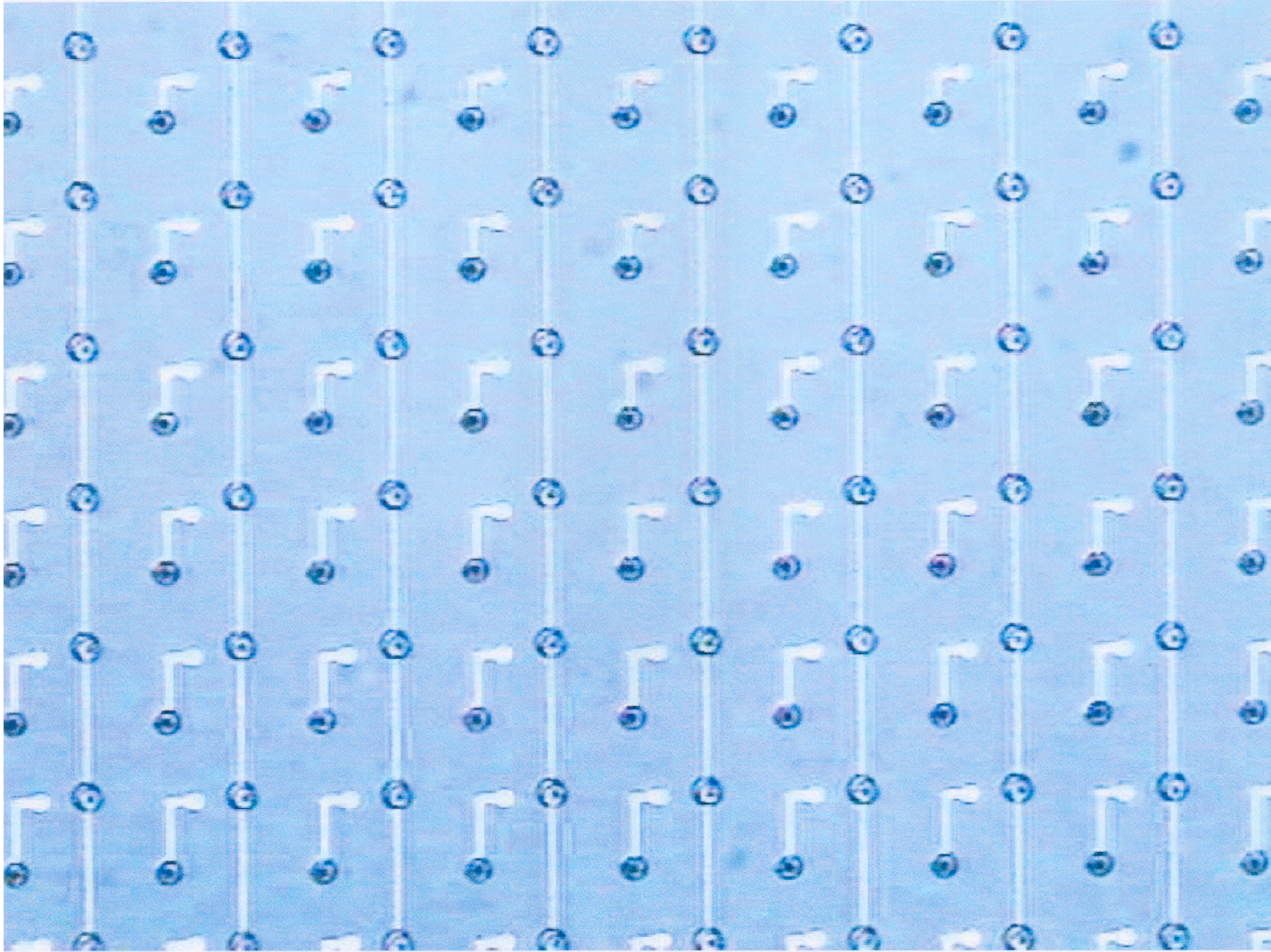


Backside
of a
64x64
planar
sensor
with
 $150\mu\text{m}$
pixels
(indium
bumps
are
applied)

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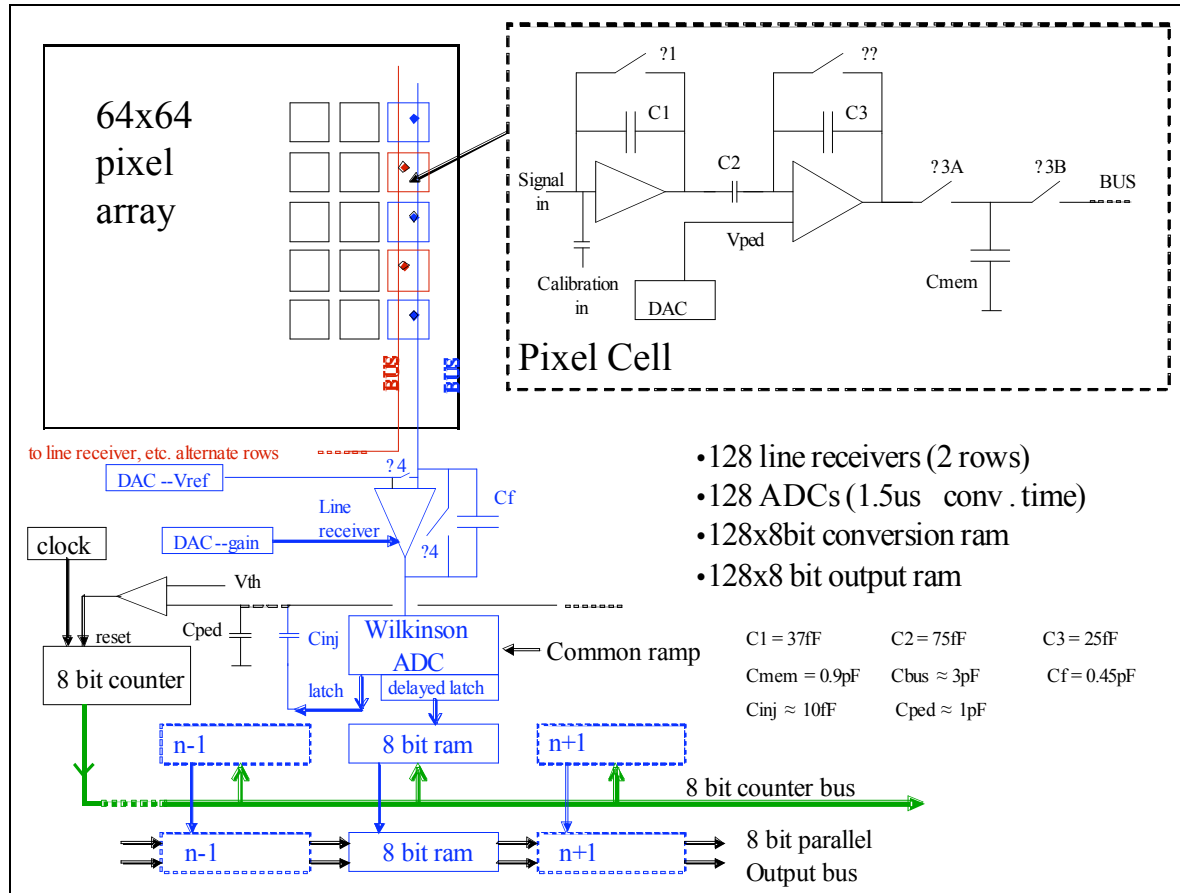


Sensor pixel
raster is
 $150\mu\text{m}$,

but readout
raster is
 $144\mu\text{m}$.

This permits
ASIC border
to remain
behind sensor
wafer

ASIC Schematic: derived from ATLAS chips: 128-fold parallel architecture, designed at LBL

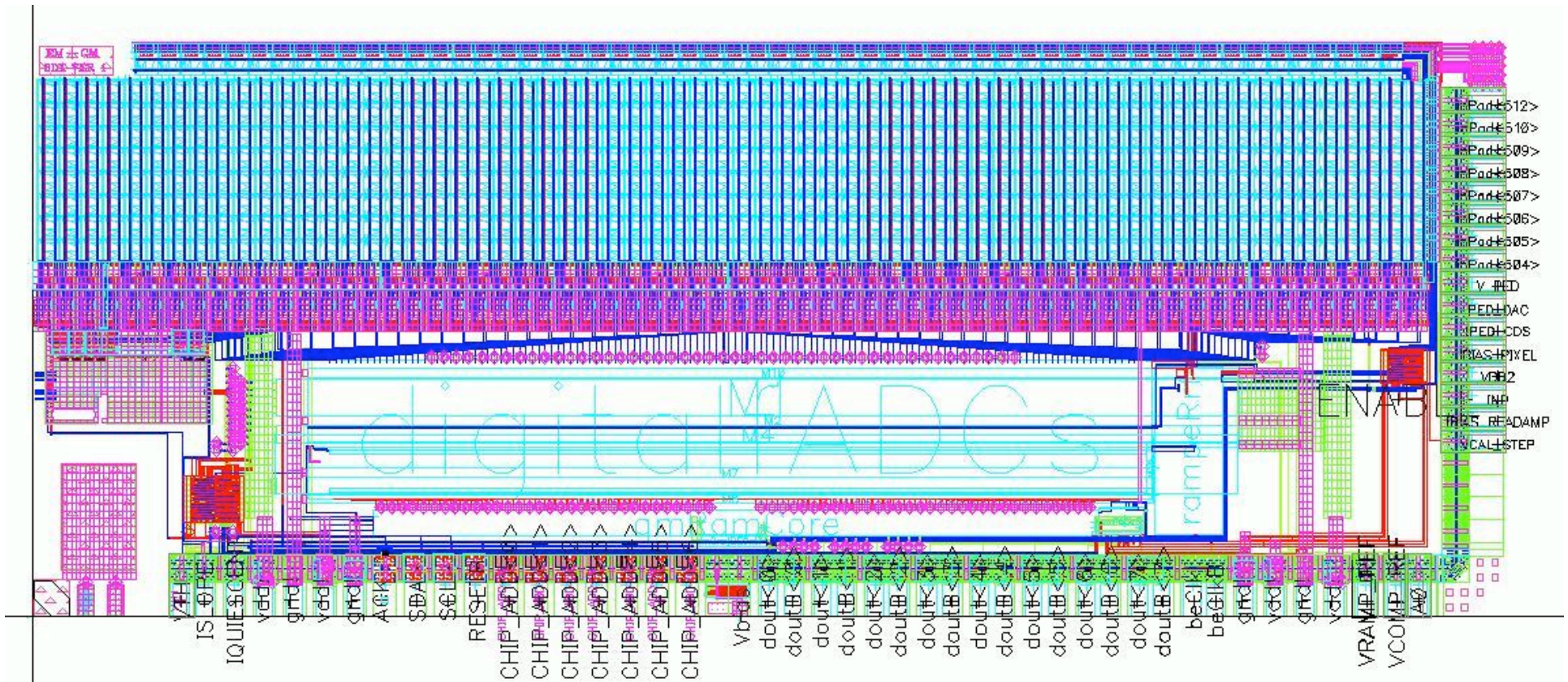


**In each pixel:
Charge preamp, gain
trim, CDS**

**6 - 8 bit ADC
encoding**

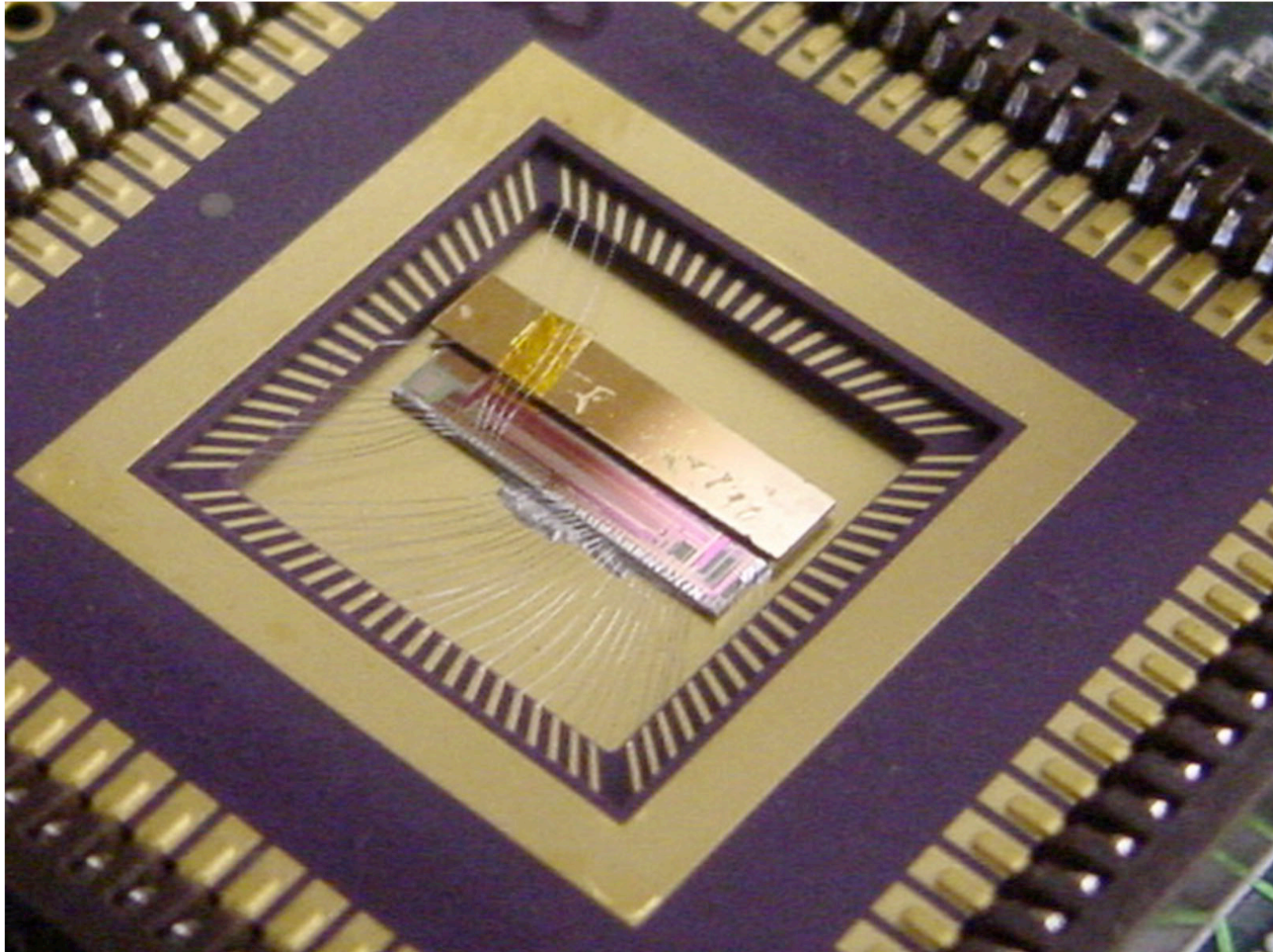
**Continuous readout
cycling, 64 μsec for
entire chip**

After 2 MOSIS runs, the ASIC works but has “bugs”.
 We currently have ~40 working ASICS.
 8 x 64 pixels in test/designASIC, to save costs
 (64th column is full length, but folded to save space).



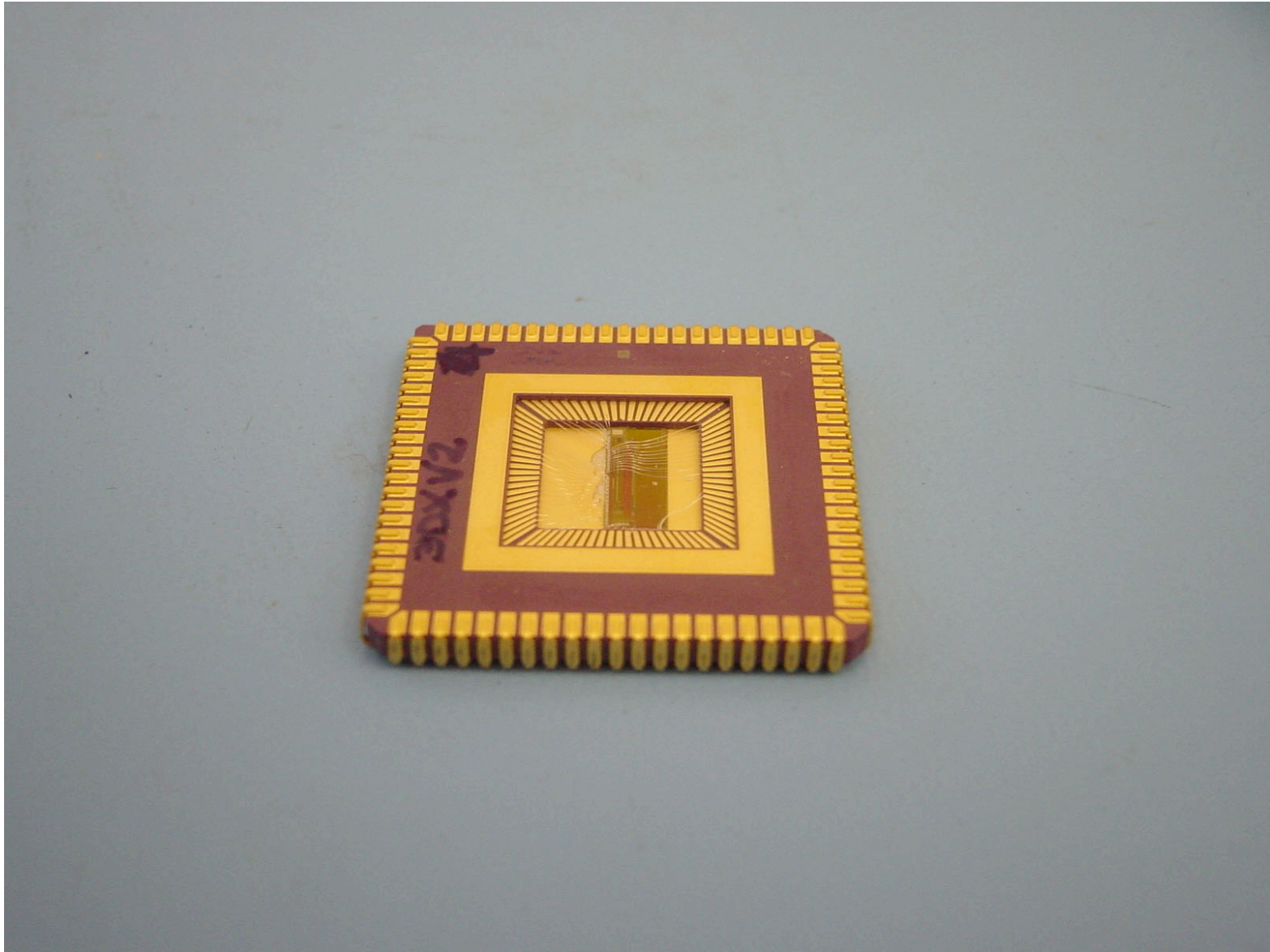
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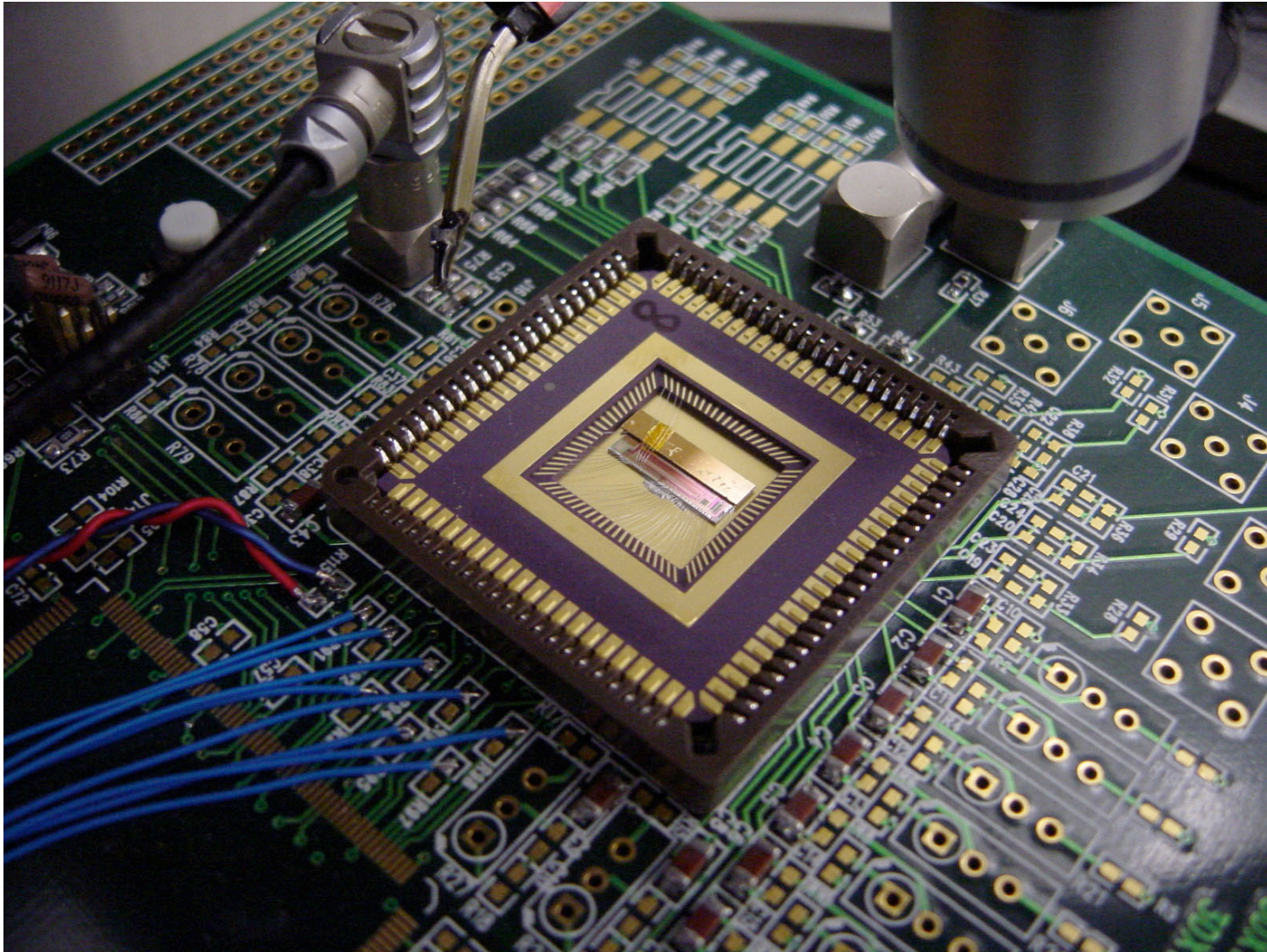
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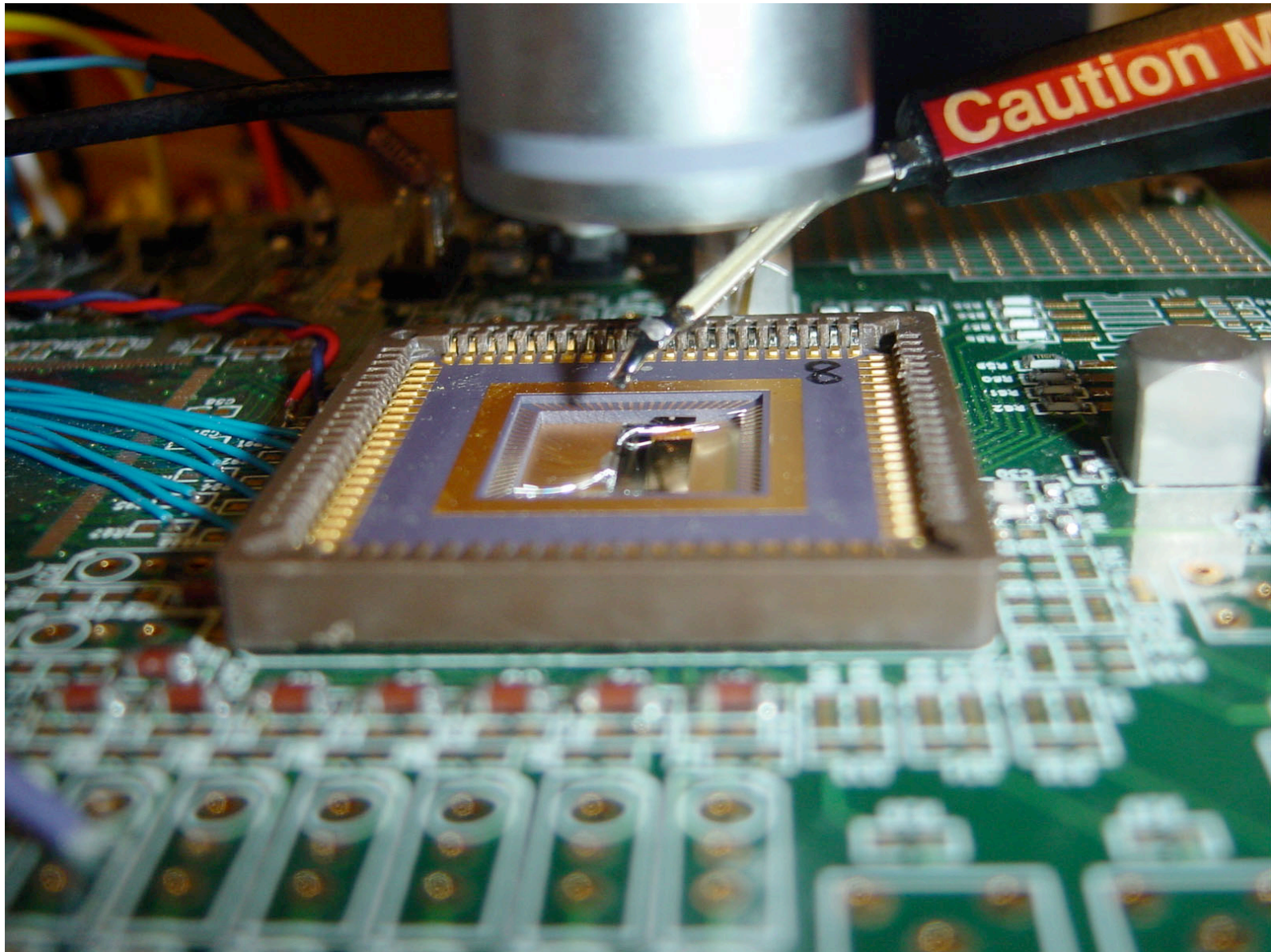
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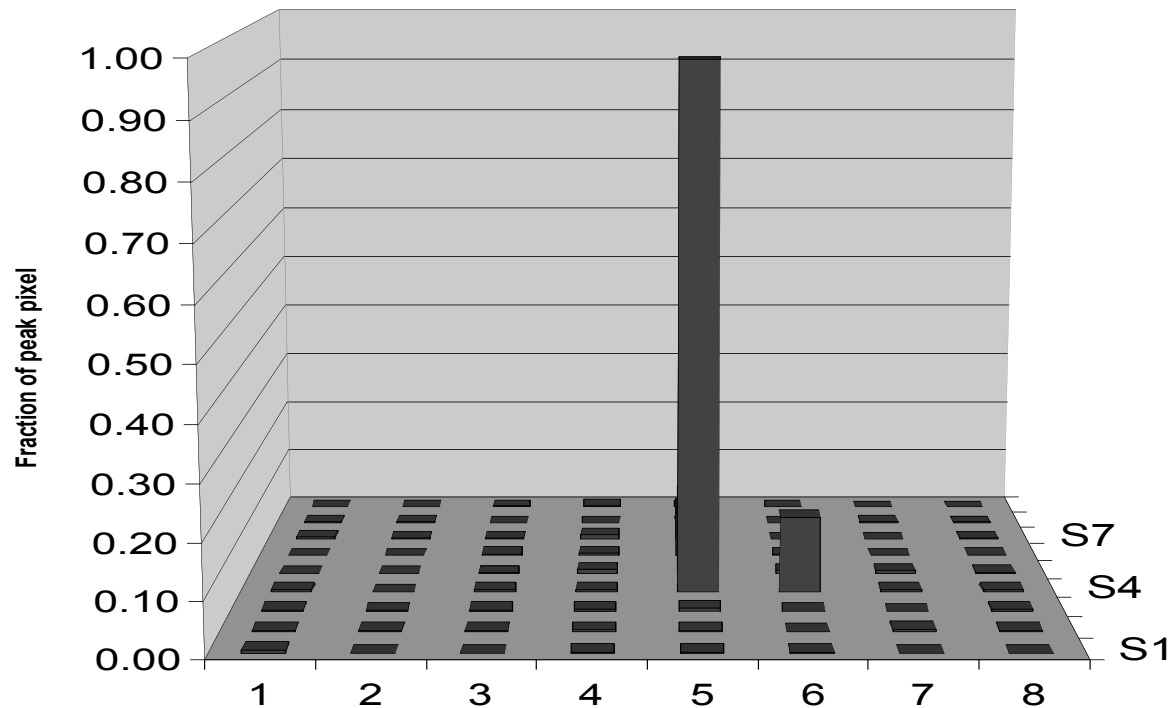




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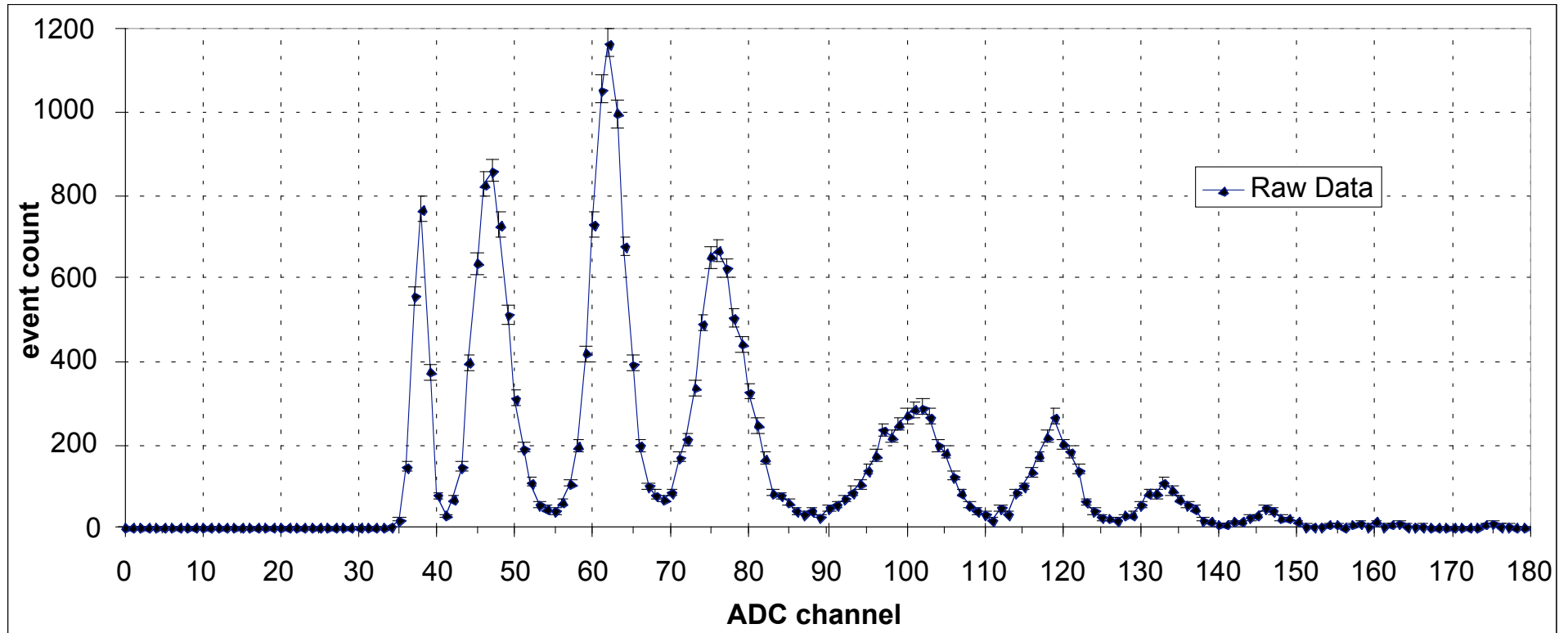
Point Response is essentially contained in a single pixel (ALS 4.2.2, $\sim 5\mu\text{m} \times 5\mu\text{m}$ slits)



Map of the 8 x 8 pixel area surrounding the aiming point of the x-ray beam.

Observed Spectral Response

(Monochromator detuned, $\sim 20,000$ photons/s)



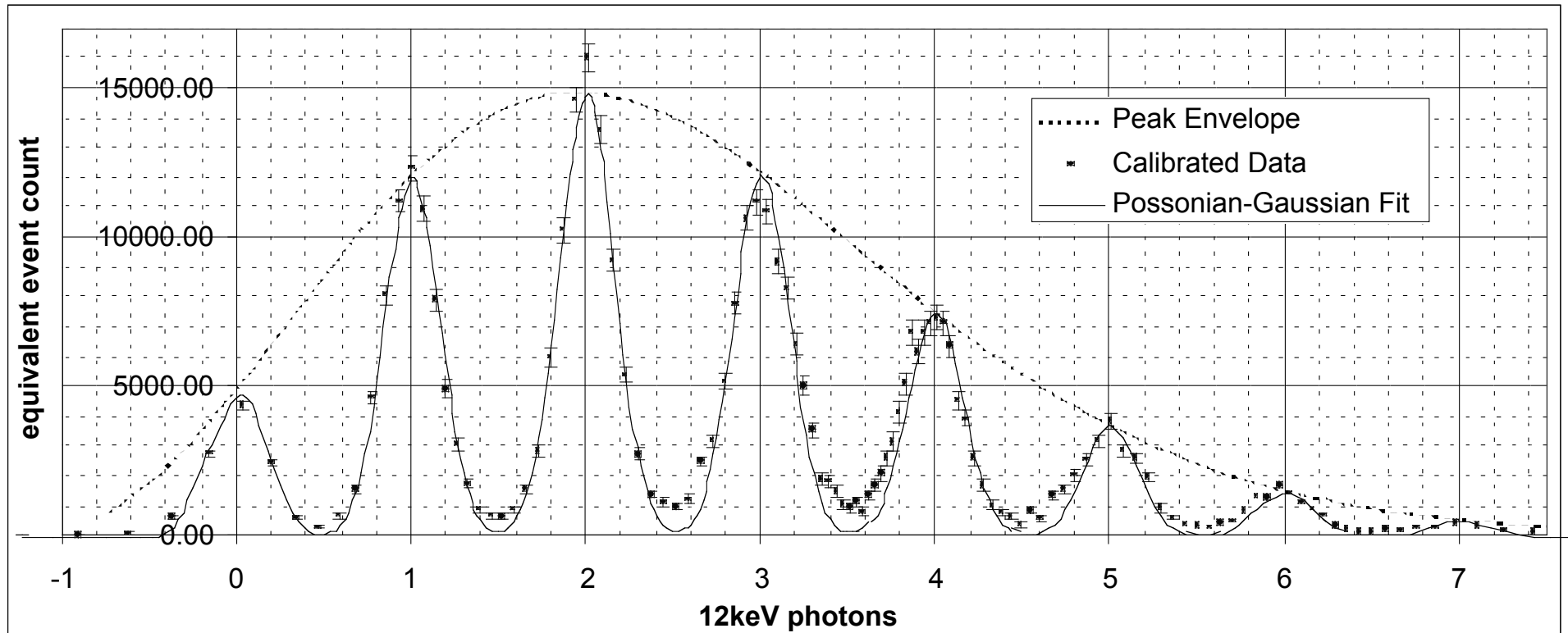
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$$P(n) = \frac{e^{-\langle n \rangle} \langle n \rangle^n}{n!}$$

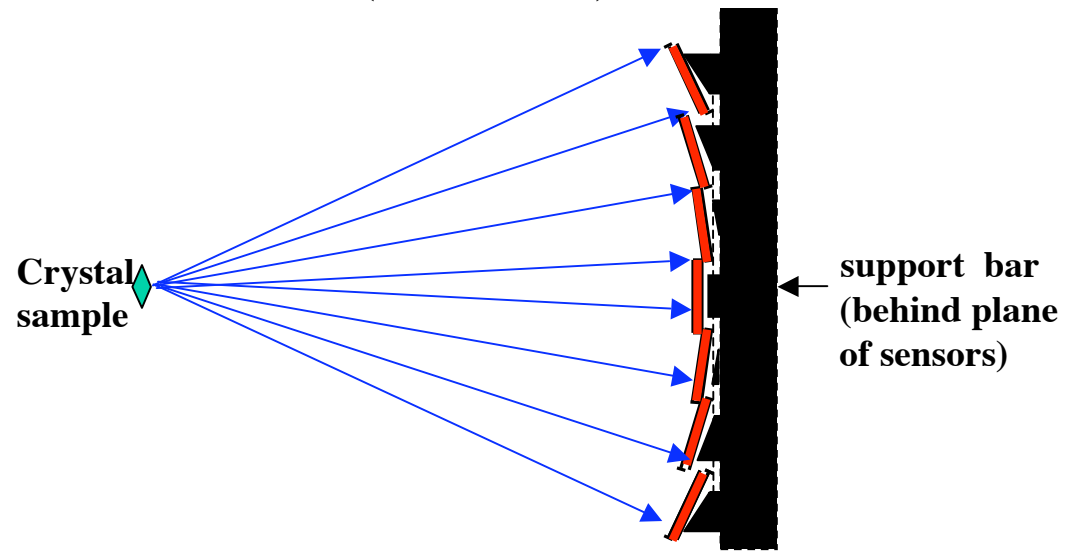
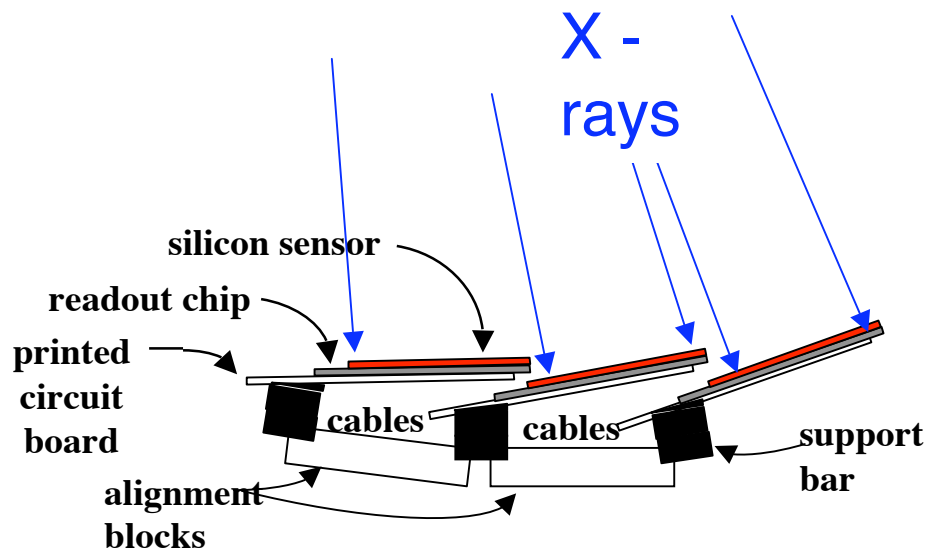
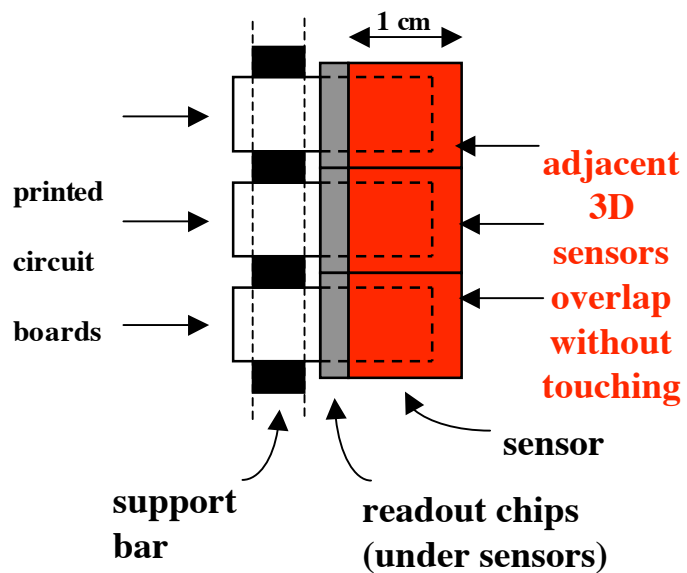
Poisson Fit to Data

$\langle n \rangle = 2.46$



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Schematic design for full scale protein crystallography detector (~300 x 300mm²)

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